

Extending InnoSwitch™3 IC Families With PowiGaN[™] Technology

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InnoSwitch3 ICs with PowiGaN[™] technology Achieve >100 W

- InnoSwitch3 silicon transistors are highly effective up to 65 W
- PowiGaN switches provide more power
 - Lower R_{DS(ON)} per unit area
 - Lower switching losses
- PowiGaN devices
 - InnoSwitch3-CP constant power
 - InnoSwitch3-EP for open-frame
 - InnoSwitch3-Pro digital control

Part Number	230 VAC ± 15%		85 - 264 VAC	
	Adapter	Open Frame	Adapter	Open Frame
INN3X74C	20 W	25 W	15 W	20 W
INN3X75C	25 W	30 W	22 W	25 W
INN3X76C	35 W	40 W	27 W	36 W
INN3X77C	40 W	45 W	36 W	40 W
INN3X68C	55 W	65 W	50 W	55 W
INN3X79C	80 W	85 W	65 W	75 W
INN3X70C	90 W	100 W	75 W	85 W

PowiGaNTM switches

PI GaN Solution are Already Used by Multiple Customers Across Many designs



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Applications Where Size and Efficiency Matters

- Aftermarket USB PD adapters
- High-end cellphone chargers and other mobile devices
- Compact notebook adapters
- Appliances, TVs, server standby, AIO PCs, video game console
- USB wall sockets, power strips and surge protectors



We Make GaN Easy to Use in Production

GaN transistors are better than silicon

- More efficient, cooler, smaller power supplies
- Leading the way to "no-heatsink" designs at high power levels
- GaN transistor technology is the future for power conversion
- Our strategy is to enclose and protect the GaN device within our ICs
 - Controller, driver, PowiGaN switch, protection, SR control all-in-one
 - Engineers see significant performance benefits
 - But won't otherwise notice a change

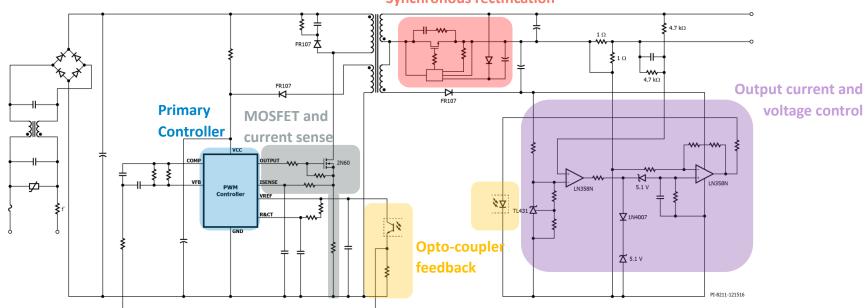




The InnoSwitch Advantage

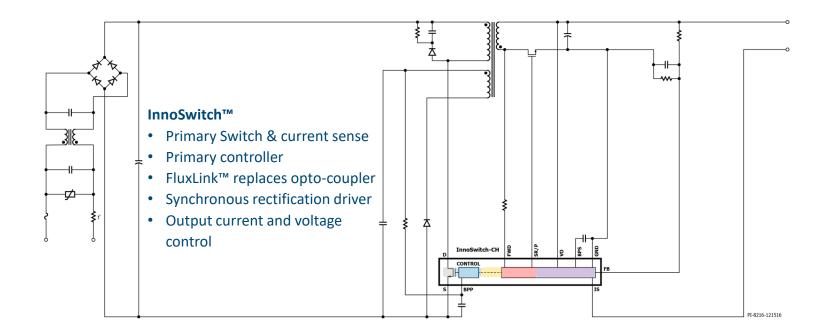
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Conventional High Efficiency Charger



Synchronous rectification

InnoSwitch High Efficiency Charger

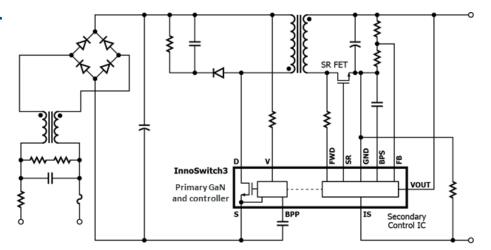




Consistent, Familiar and Easy to Implement

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- Same simple flyback circuit topology
- Use identical SMPS design flows for silicon and PowiGaN InnoSwitch3 ICs
- Identical switching frequency
- External components scale for power
- Switching waveforms are the same
- No unusual behaviors or concerns
 - EMI Standard techniques
 - ESD No different from silicon

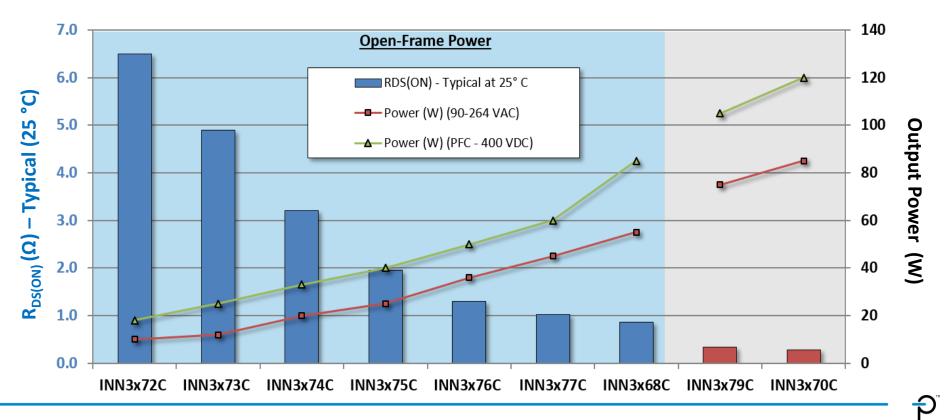


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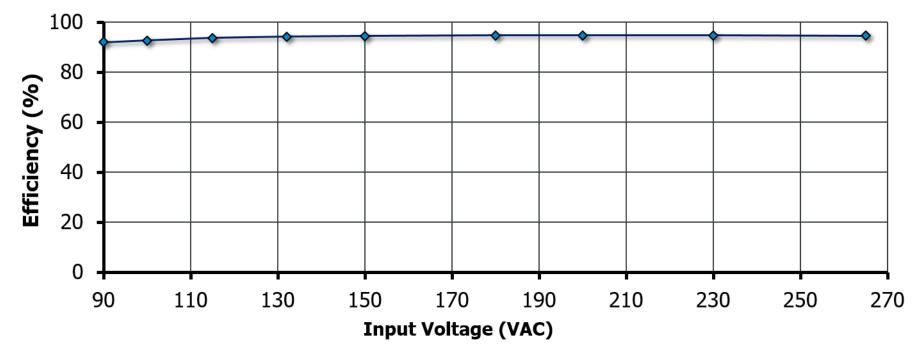
PowiGaN Increases Performance of Industry-Leading InnoSwitch-3 ICs

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PowiGaN Increases Efficiency and Power



PowiGaN Design Achieves 95% Full-Load Efficiency -Eliminates Heatsink from Adapter

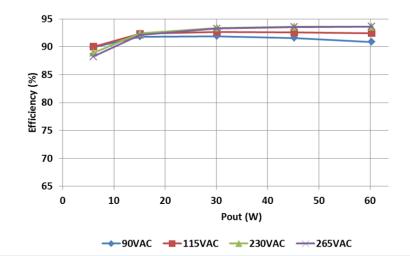


DER-747 (65 W, 20 V Adapter): Full-load efficiency is 95% at 230 VAC and 94% at 115 VAC

PowiGaN High Efficiency Also Improves Performance Across Load for 60 W USB PD

Same high-efficiency-across-load as standard InnoSwitch3

- Ideal for high-power USB PD applications
- Average efficiency is 92.49% at 115 VAC and 93.24% at 230 VAC



PowiGaN Reference Designs Available Now

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Use InnoSwitch3 for PD-only designs

- DER-601: 60 W USB-PD (WT6615F)
- ▶ DER-602: 100 W USB-PD (WT6633P)
- DER-751: 132 W PSU for multi-port USB-PD adapter
- DER-747: 65 W 20 V / 3.25 A adapter

Use InnoSwitch3-Pro for <u>PD + PPS</u> designs

- DER-802: 60 W USB-PD (WT6635P)
- DER-803: 60 W USB-PD (VP302)
- DER-805: 100 W USB-PD (VP302)





PI Expert Now Supports PowiGaN Devices

Creates real-time custom solutions that match customer specifications

- Provides design that is fully functional across operating conditions, start-up & overload
- Complete schematic –including EMI filtering and heatsinking guidance
- Bill of material is user-adjustable to accommodate preferred components
- Transformer documentation and full build information

Free download from PI website

PI Expert[™] Online ふ





PowiGaN – Powerful, Efficient, Reliable

PowiGaN devices deliver more power

- Reduced on-resistance
- Lower switching loss
- Operation indistinguishable InnoSwitch-3 silicon devices
- Manufacturing processes developed and maintained by PI
 - Working with established partners
- Industry-leading GaN qualification process
- Shipping in high volume production now

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